

## Multizone, Multiobject D-TOF System in 55nm

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### Content

Sensing is life.

- Time of flight module
  - Silicon
    - » Sensor
      - SPAD
      - Readout
      - Time to Digital Converter
      - Data storage
    - » Illumination
      - VCSEL driver
- Measurement Results
  - VCSEL beam
  - Distance measurement
    - » Module only, cover glass, smudge
- Demonstration video
  - » Distance measurement
  - » Multi object
  - » Multi zone



### D-TOF Silicon SPAD sensor and light emitter

- Architecture
- Characterization data

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### **Block Diagram**





2 Low Voltage Power High Voltage Power Breakdown voltage Management Management detection 2 2 ... TDC+Memory TDC+Memory SPAD I2C interface 88 array 5 П ••• ... 2 2 ... SPAD SPAD array array TDC+Memory 55 5 5 CPU • • • ... g Q ••• ARM MO ... SPAD SPAD array array ....É 🖸 2 ... Main Memory TDC+Memory TDC+Memory V/I Clock VCSEL Driver Reference Generation

Features:

- 55nm HV process node
- Custom developed SPAD sensor
- 4 zones on main sensor array
- TDC and histogram based distance detection
- Fully integrated power management
- Cortex M0 CPU
- Sub-ns pulse generating laser driver
- Multi-mesa VCSEL diode

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### **SPAD** Details



#### **SPAD cross section:**



**SPAD** characteristics:

Parameter	Тур	Unit
BV	17.7	V
BV temperature coefficient	0.016	V/K
DCR @ 3V	0.28	cps/um <sup>2</sup>
PDP @ 940nm	1.5	%
Timing Jitter @ 940nm (FWHM)	80	ps
After pulsing probability	<0.5	%
Fill factor (SPAD + Quenching)	25	%

- Isolated SPAD sensor
- Modified process to generate SPAD P and SPAD N layer to reduce the breakdown voltage
  - + Iow DCR
  - + low jitter
  - + Low afterpulsing probability

### SPAD Key Characteristics PDP=f(V<sub>exc</sub>, T, λ)

- Photon detection probability PDP depends on wavelength and excess bias voltage.
- PDP increases with temperature for 940nm because bandgap decreases with temperature.
- PDP similar to state of the art.





(†) Veerappan, C., Charbon, E., "A Low Dark Count p-i-n Diode Based SPAD in CMOS Technology," IEEE Trans. Electron Devices 63(1), 65–71 (2016).

### **SPAD Key Characteristics**

#### **Timing Jitter @940nm**

- The full width half maximum (FWHM) of the timing jitter ٠ decreases with excess bias voltage.
- The jitter tail is hardly impacted by the excess bias voltage.
- The FWHM at 3V excess bias voltage is 80ps including the jitter from the Laser source (42ps).





-1.5

-----2

<del>~~</del>3

-5



### Distance Measurement Readout and Time-to-Digital converter



- SPAD readout circuitry
- Symmetrical digital gates
  - TDC principle
  - TDC architecture
- Distance processing and calibration
  - Histogram storage

### Sensor Readout

#### **Overview**





- Pulse shaper to generate a narrow event pulse independent on SPAD deadtime
- Multiple SPADs to be combined to a single TDC channel by using an OR-Tree
- Readout time must be equal from each SPAD to the TDC



## Time to Digital Converter

#### **Overview**



## Free running ring oscillator with flip-flop based overflow counter and latches

- Fine Counter:
- LSB represents propagation delay of inverting cell (~50ps)
- Coarse Counter:
  - Flip-flop based counter detecting overflow of fine counter
- Latch:
  - To store the actual state of the counter on-the-fly without disturbing oscillation
- Decoder: decode
  - Combines fine- and coarse- counter value to a timestamp
- Data is stored in SRAM based histogram memory
  - » Counter value represent address to be incremented



#### TDC core architecture:





# **TDC** Principle I

#### **Simplified Example**



- Transparent latches immediately freeze counter values in case of an event
- High probability that one latch of the fine counter is in metastable state
  - could introduce 1LSB error **》**
- Coarse counter setup time causes delayed response on fine counter overflow
  - Unsafe region of counter may **》** introduce large error



## **TDC Principle II**

#### **Simplified Example**







- 2 flip-flop based overflow counters with complimentary clock edge sensitivity
  - Consider only the "stable" coarse counter of a oscillation period when evaluating the latched counter value of the TDC at point in time of trigger signal
    - Fine counter values indicates region and therefore coarse counter to be used
    - Coarse counter value need to be corrected in certain region to cover overlap
  - Overall 1 LSB error could be introduced

#### How to calibrate the fine counter?

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## **TDC** Calibration

#### **Digital Calibration Scheme**

#### **Before calibration**



#### After calibration





- Each TDC contains one ring oscillator
- Absolute ring oscillator speed is unknown (-50%..+100%)
- Relative ring oscillator speed amongst each other (+-5%)
- Pure digital solution for calibration is used.
  - Each TDC is able to measure its own ring oscillator speed using the system clock as reference.
  - Correction factor can be determined for individual histograms



### Illumination of scene VCSEL and VCSEL Driver

- VCSEL architecture
  - VCSEL driver
- Optical characteristics of beam

### **VCSEL** Driver

#### **Key Performance Parameter**



#### **Block Diagram**



- Charge Pump
  - Decouples min supply voltage from VCSEL forward voltage
  - Small loop of VCSEL current (low EMI)
  - No extra PMOS switch required
- Eye Safety Control
  - Short on VCSEL anode/cathode
  - Current limitation through VCSEL (charge pump)
  - Clock failure detection (charge pump)
- Pulse generation
  - Pulse width: ~300ps FWHM
  - High peak current
- Laser safety: Class 1



### System performance Measurement results

- VCSEL pulse
- Crosstalk and smudge removal
- High accuracy, Independent of object color
  - Demonstration video

## VCSEL beam measurements



#### Optical pulse



VCSEL emission profile



Characteristics:

- Optical pulse 150ps
- FOI 15° (1/e<sup>2</sup>)

• Sub-ns pulsed mode allows increased peak power

## Measurement conditions

#### 200mm to 3000mm in 50mm steps

- Target size:
  - 1m x 1m
  - 50fps/800 000 integration cycles
- Color:
  - 90% white
  - 18% grey
  - 4% black
- Conditions:
  - Without cover glass
  - With cover glass (85% transmissivity)
  - Cover glass + smudge
- Background light on the target:
  - 0.2klux
  - 1klux
  - 5klux
  - 10klux
  - 20klux





## Histogram comparison

without background light

#### without Coverglass



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## Distance measurement I



#### 0.2klux and 1klux





### Distance measurement II



#### 5klux, 10klux and 20klux



### Conclusion

- Direct Time of Flight system using robust histogram-based architecture
- Custom developed SPAD sensor in 55nmHV process node
- Symmetrical readout structure
- Free running TDC architecture
  - Digital calibration scheme
  - Double differential measurement principle
- 940nm VCSEL laser in pulsed operation
  - Laser class 1 safe
- Distance measurement over a wide range of conditions
  - Distance measurement insensitive to crosstalk and smudge
- Multi-object
- Multi-zone capability







# Thank you!

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